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(54) Title: HIGH-TRANSPARENCY SEMICONDUCTOR-METAL INTERFACES

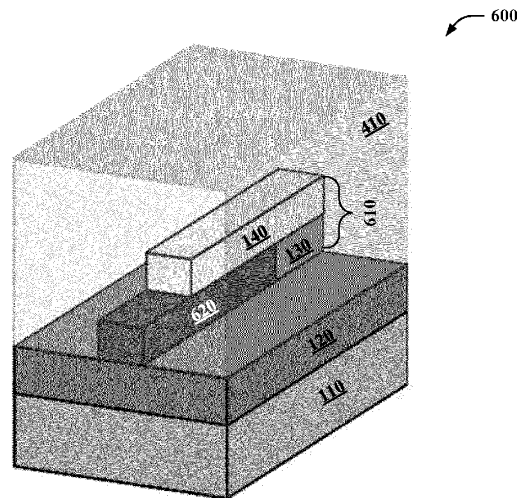


FIG. 6

(57) Abstract: Techniques that can facilitate high-transparency semiconductor-metal interfaces are provided. In one example, a method can comprise forming a silicon on insulator (SOI) over a wafer. The method can further comprise depositing a metal on the SOI. The method can further comprise forming a structure by dry-etching the metal and dry-etching the SOI. The method can further comprise forming a template over the structure. The method can further comprise etching a portion of the SOI for removal under the metal. The method can further comprise growing a semiconductor where the portion of SOI was removed.

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